L Number	Hits	Search Text	DB	Time stamp
3	3330	(control near gate) and (source and drain) and memory and (ONO (oxide-nitride-oxide) (oxide/nitride/oxide) (silicon near oxide/silicon near nitride/silicon near oxide)) and (@ad<20030514 @rlad<20030514)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/21 13:49
4	533630	((insulat$3 dielectric) near (layer film)) SOI (silicon near on near insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/21 13:50
5	3048	((control near gate) and (source and drain) and memory and (ONO (oxide-nitride-oxide) (oxide/nitride/oxide) (silicon near oxide/silicon near nitride/silicon near oxide)) and (@ad<20030514 @rlad<20030514)) and (((insulat$3 dielectric) near (layer film)) SOI (silicon near on near insulator))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/21 13:53

C:\APPS\east\workspaces\10604613-multilevel.wsp